

Lecture 22: I/O

Outline

- ❑ Basic I/O Pads
 - ❑ I/O Channels
 - Transmission Lines
 - Noise and Interference
 - ❑ High-Speed I/O
 - Transmitters
 - Receivers
 - ❑ Clock Recovery
 - Source-Synchronous
 - Mesochronous
-

Input / Output

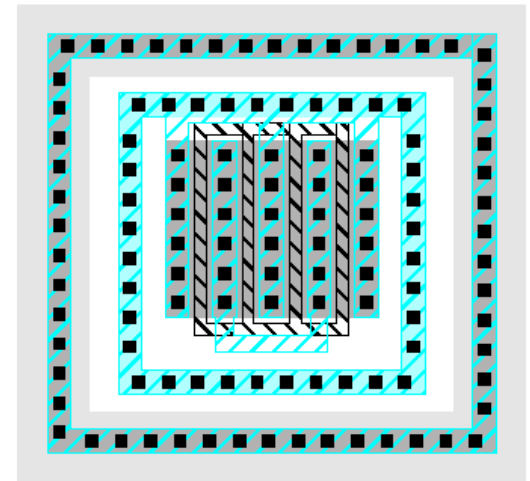
- ❑ Input/Output System functions
 - Communicate between chip and external world
 - Drive large capacitance off chip
 - Operate at compatible voltage levels
 - Provide adequate bandwidth
 - Limit slew rates to control di/dt noise
 - Protect chip against electrostatic discharge
 - Use small number of pins (low cost)

I/O Pad Design

- Pad types
 - V_{DD} / GND
 - Output
 - Input
 - Bidirectional
 - Analog

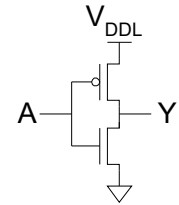
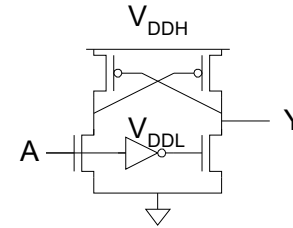
Output Pads

- ❑ Drive large off-chip loads (2 – 50 pF)
 - With suitable rise/fall times
 - Requires chain of successively larger buffers
- ❑ Guard rings to protect against latchup
 - Noise below GND injects charge into substrate
 - Large nMOS output transistor
 - p+ inner guard ring
 - n+ outer guard ring
 - In n-well

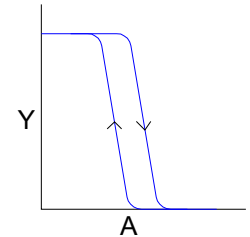
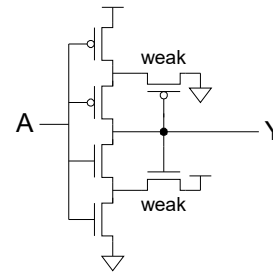


Input Pads

- ❑ Level conversion
 - Higher or lower off-chip V
 - May need thick oxide gates



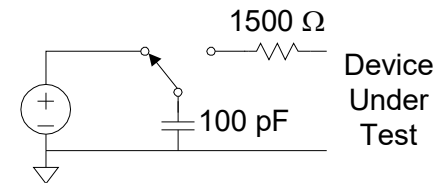
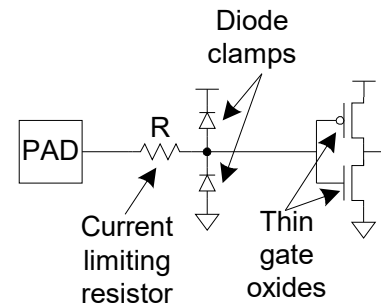
- ❑ Noise filtering
 - Schmitt trigger
 - Hysteresis changes V_{IH} , V_{IL}



- ❑ Protection against electrostatic discharge

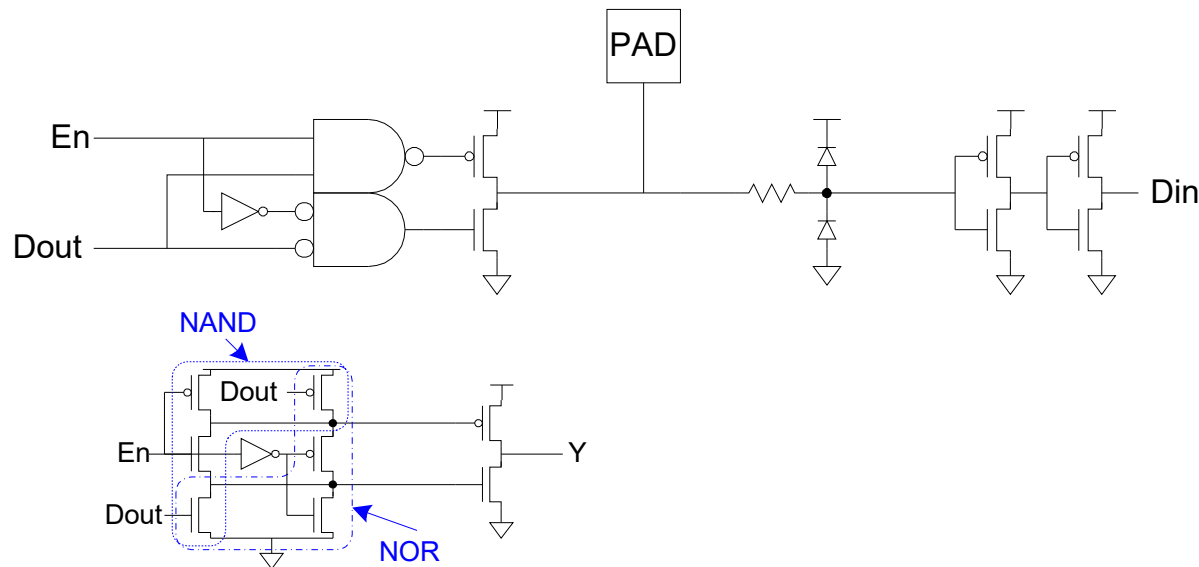
ESD Protection

- ❑ Static electricity builds up on your body
 - Shock delivered to a chip can fry thin gates
 - Must dissipate this energy in protection circuits before it reaches the gates
- ❑ ESD protection circuits
 - Current limiting resistor
 - Diode clamps
- ❑ ESD testing
 - Human body model
 - Views human as charged capacitor



Bidirectional Pads

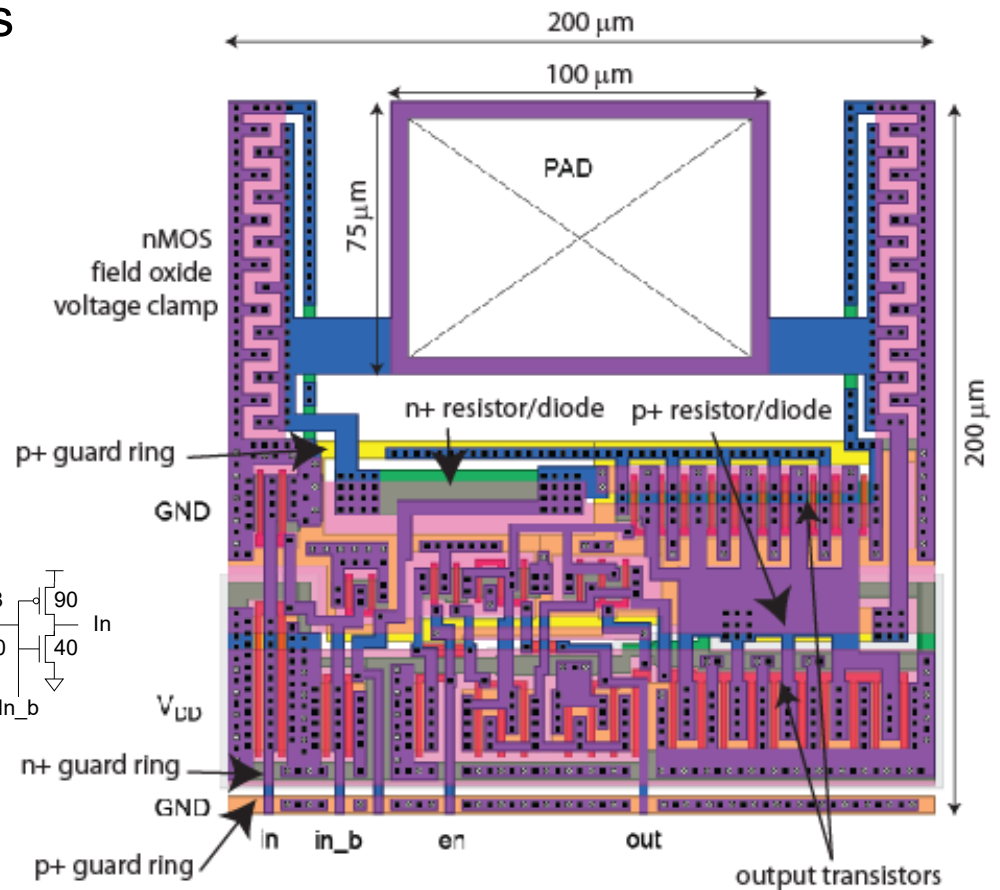
- ❑ Combine input and output pad
- ❑ Need tristate driver on output
 - Use enable signal to set direction
 - Optimized tristate avoids huge series transistors



Analog Pads

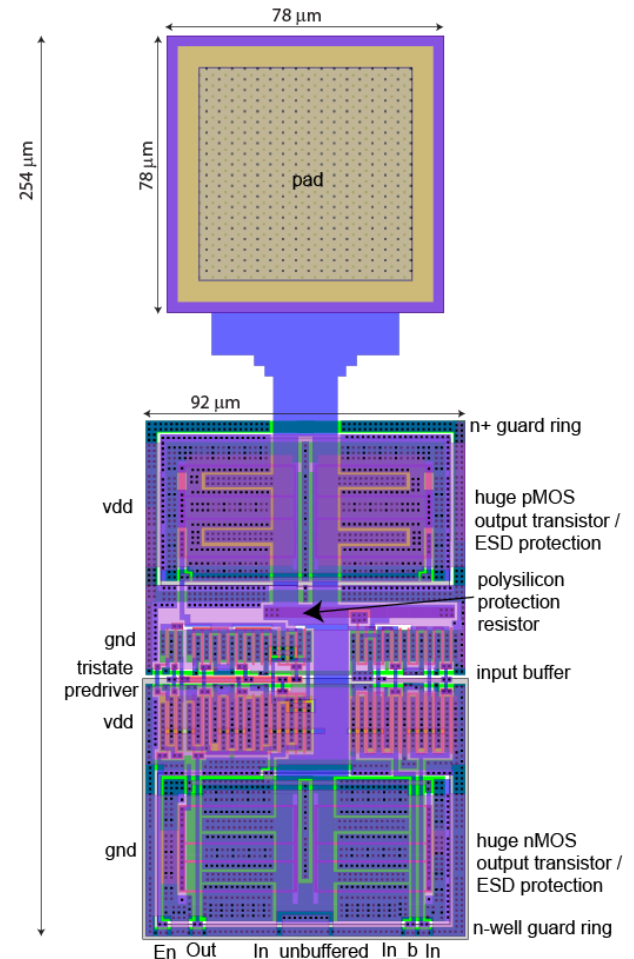
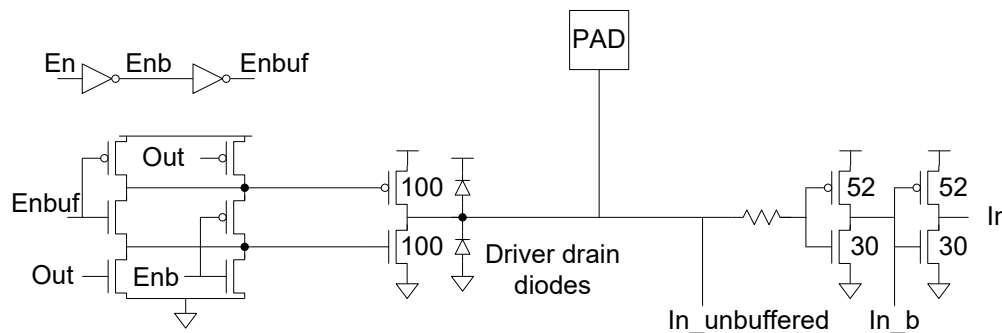
- ❑ Pass analog voltages directly in or out of chip
 - No buffering
 - Protection circuits must not distort voltages

- ❑ 1.6 μm two-metal process
 - Protection resistors
 - Protection diodes
 - Guard rings
 - Field oxide clamps



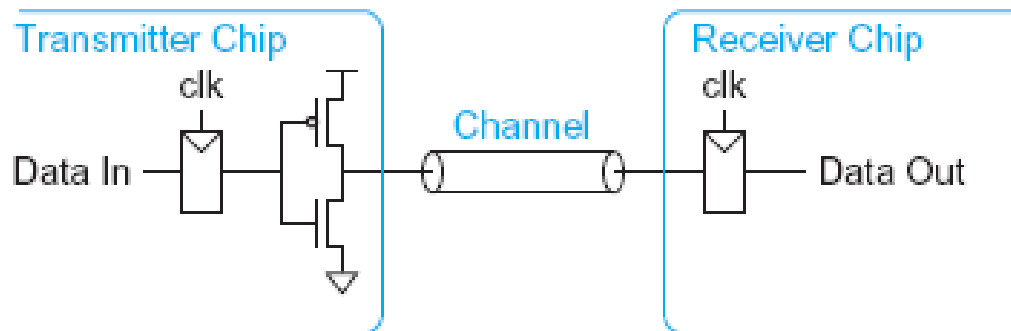
UofU I/O Pad

- ❑ 0.6 μm three-metal process
 - Similar I/O drivers
 - Big driver transistors provide ESD protection
 - Guard rings around driver



I/O Channels

- ❑ I/O Channel: connection between chips
 - Low frequency: ideal equipotential net
 - High frequency: transmission line
- ❑ Transmission lines model
 - Finite velocity of signal along wire
 - Characteristic impedance of wire



When is a wire a T-Line?

- ❑ When propagation delay along the wire is comparable to the edge rate of the signal propagating
- ❑ Depends on
 - Length
 - Speed of light in the medium
 - Edge rate

Example

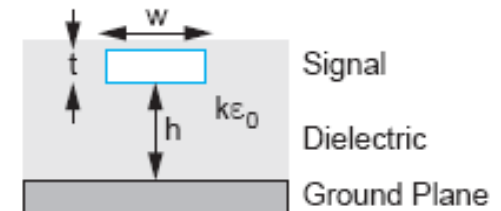
- ❑ When must a 10 cm trace on a PCB be treated as a transmission line
 - FR4 epoxy has $k = 4.35$ ($\epsilon = k\epsilon_0$)
 - Assume rise/fall times are $\frac{1}{4}$ of cycle time
- ❑ Signal propagation velocity
$$v = \frac{c}{\sqrt{4.35}} = \frac{3 \times 10^8 \frac{\text{m}}{\text{s}}}{2.086} = 14.4 \frac{\text{cm}}{\text{ns}}$$
- ❑ Wire flight time
$$t = \frac{10 \text{ cm}}{14.4 \frac{\text{cm}}{\text{ns}}} = 0.7 \text{ ns}$$
- ❑ Thus the wire should be treated as a transmission line when signals have a period $< 2.8 \text{ ns}$ ($> 350 \text{ MHz}$)

Characteristic Impedance

- ❑ Z_0 : ratio of voltage to current of a signal along the line
- ❑ Depends on the geometry of the line

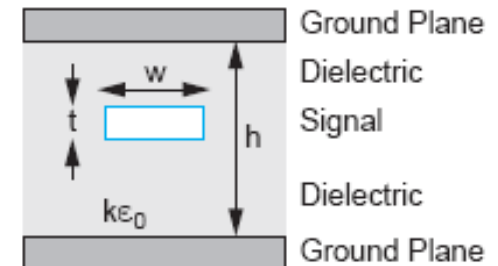
Microstrip: Outer layer of PCB

$$Z_0 = \frac{60}{\sqrt{0.457k + 0.67}} \ln \frac{4h}{0.67(0.8w + t)}$$



Stripline: Inner layer of PCB

$$Z_0 = \frac{60}{\sqrt{k}} \ln \frac{4h}{0.67\pi(0.8w + t)}$$



Example

- ❑ A 4-layer PCB contains power and ground planes on the inner layers and signals on the outer layers. The board uses 1 oz copper (1.4 mils thick) and the FR4 dielectric is 8.7 mils thick. How wide should the traces be to achieve 50 Ω characteristic impedance?
- ❑ This is a microstrip design. Solve for w with
 - $t = 1.4$ mils
 - $h = 8.7$ mils
 - $k = 4.35$
 - $Z_0 = 50 \Omega$
- ❑ $w = 15$ mils

$$Z_0 = \frac{60}{\sqrt{0.457k + 0.67}} \ln \frac{4h}{0.67(0.8w + t)}$$

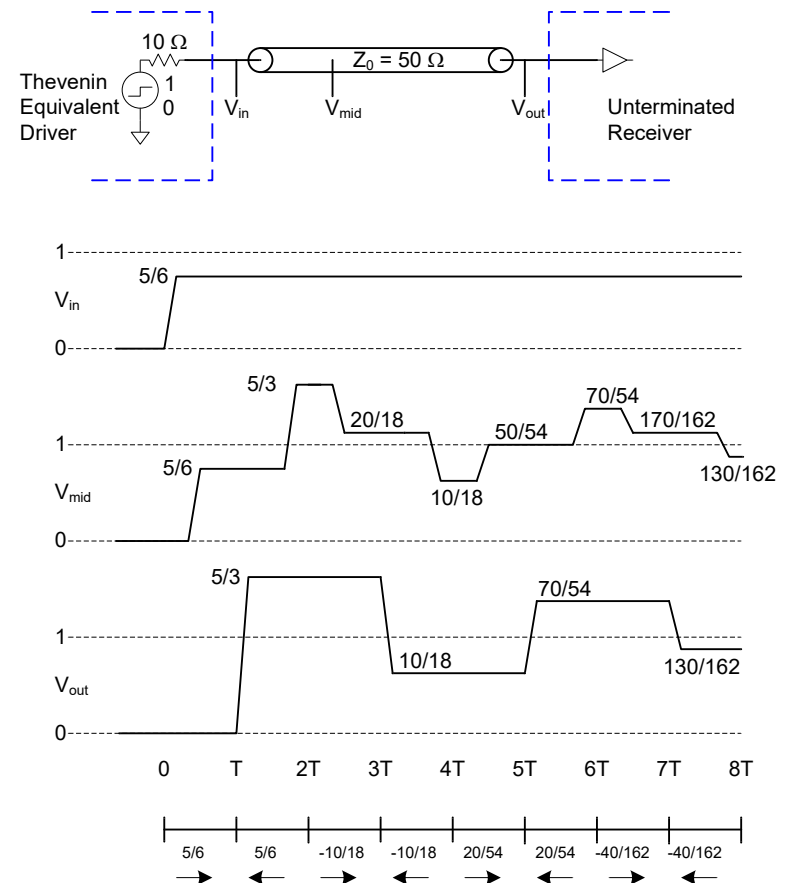
Reflections

- ❑ When a wave hits the end of a transmission line, part of the energy will reflect if the load impedance does not match the characteristic impedance.
- ❑ Reflection coefficient: $\Gamma = \frac{Z_L - Z_0}{Z_L + Z_0}$
- ❑ A wave with an amplitude of $V_{\text{reflected}} = \Gamma V_{\text{incident}}$ returns along the line.

Example: Reflections

- ❑ A strong driver with a Thevenin equivalent resistance of $10\ \Omega$ drives an unterminated transmission line with $Z_0 = 50\ \Omega$ and flight time T . Plot the voltage at the 1/3 point and end of the line.
- ❑ Reflection coefficients:

$$\Gamma_S = \frac{10 - 50}{10 + 50} = -\frac{2}{3}; \quad \Gamma_L = \frac{\infty - 50}{\infty + 50} = 1$$
- ❑ Initial wave: $50/(10+50) = 5/6$
- ❑ Observe ringing at load



Intersymbol Interference

- ❑ Must wait until reflections damp out before sending next bit
- ❑ Otherwise, *intersymbol interference* will occur
- ❑ With an unterminated transmission line, minimum bit time is equal to several round trips along the line

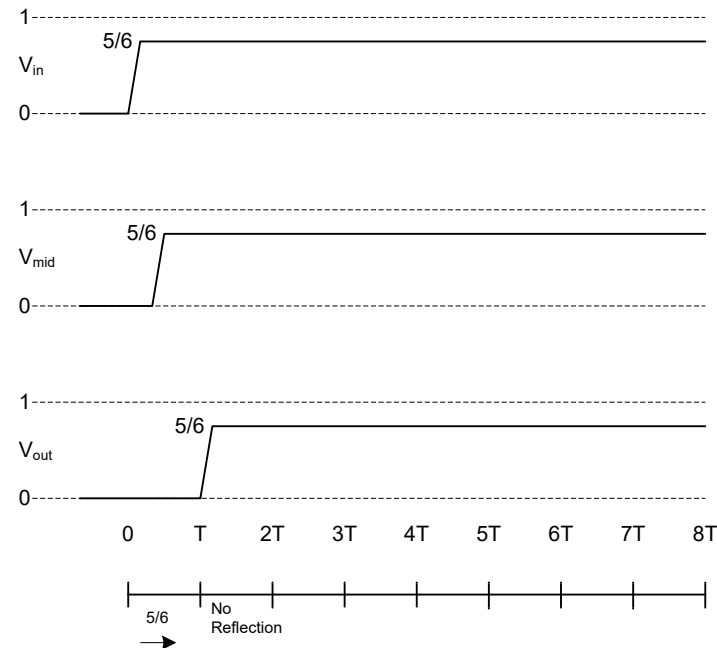
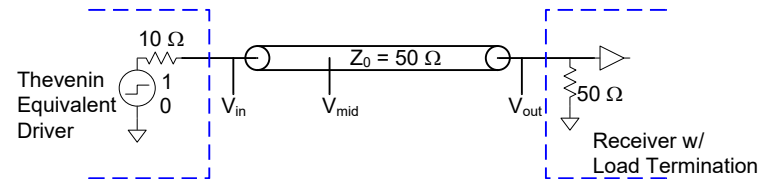
Example: Load Termination

- Redo the previous example if the load is terminated with a 50 Ω resistor.

- Reflection coefficients:

$$\Gamma_S = \frac{10 - 50}{10 + 50} = -\frac{2}{3}; \quad \Gamma_L = \frac{50 - 50}{50 + 50} = 0$$

- Initial wave: $50/(10+50) = 5/6$
- No ringing
- Power dissipation in load resistor



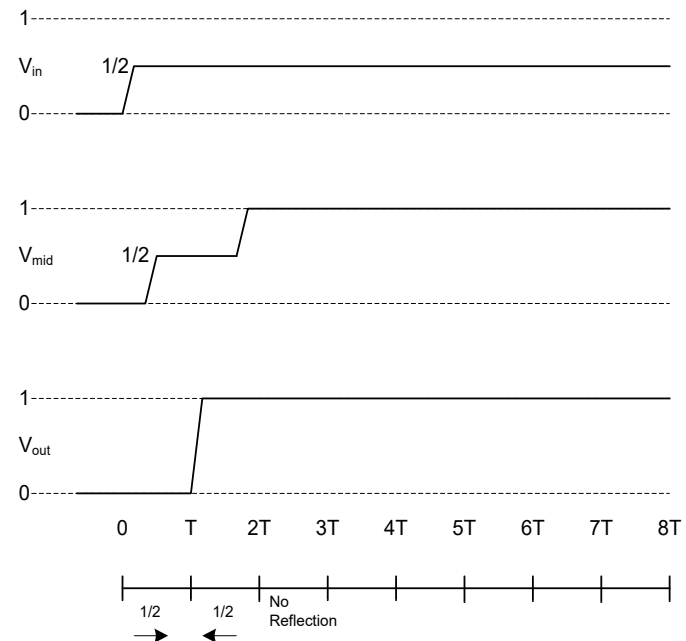
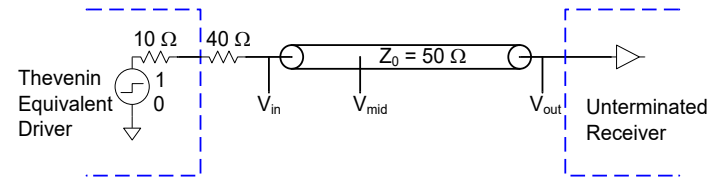
Example: Source Termination

- Redo the previous example if the source is terminated with an extra $40\ \Omega$ resistor.

- Reflection coefficients:

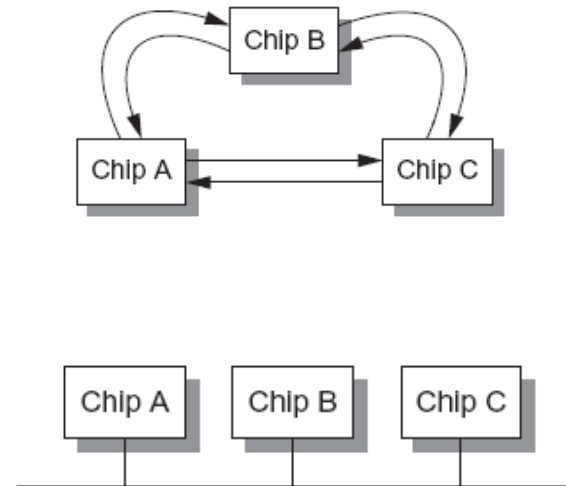
$$\Gamma_S = \frac{50 - 50}{50 + 50} = 0; \quad \Gamma_L = \frac{\infty - 50}{\infty + 50} = 1$$

- Initial wave: $50/(50+50) = 1/2$
- No ringing
- No power dissipation in load
- Taps along T-line momentarily see invalid levels



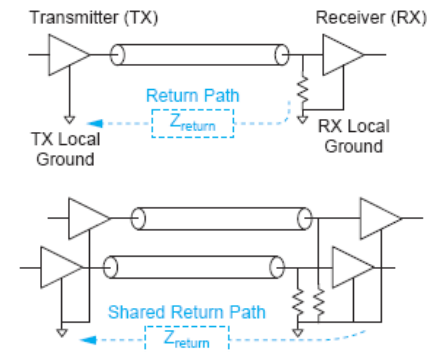
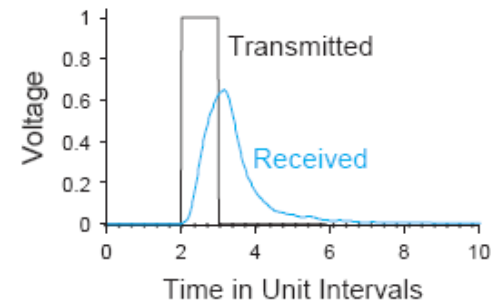
Termination Summary

- ❑ For point-to-point links, source terminate to save power
- ❑ For multidrop busses, load terminate to ensure valid logic levels
- ❑ For busses with multiple receivers and drivers, terminate at both ends of the line to prevent reflections from either end



Noise and Interference

- ❑ Other sources of intersymbol interference:
 - Dispersion
 - Caused by nonzero line resistance
 - Crosstalk
 - Capacitive or inductive coupling between channels
 - Ground Bounce
 - Nonzero return path impedance
 - Simultaneous Switching Noise



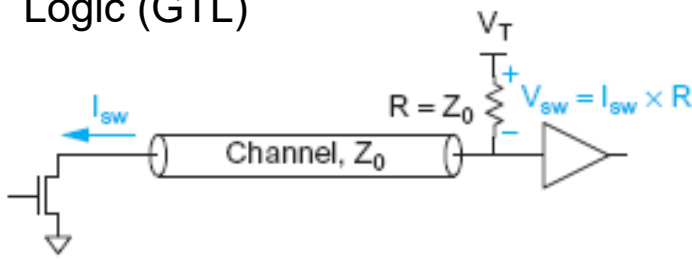
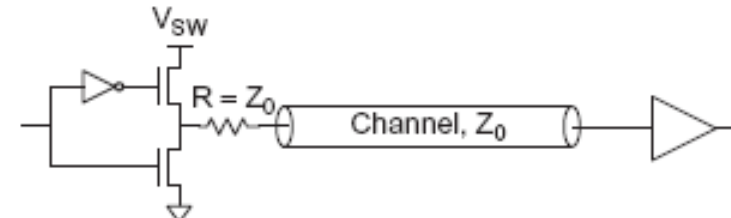
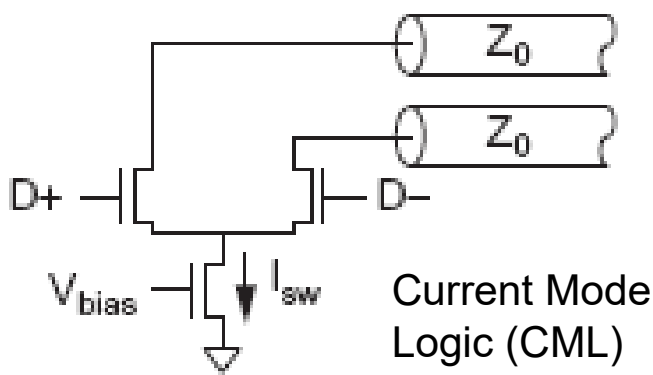
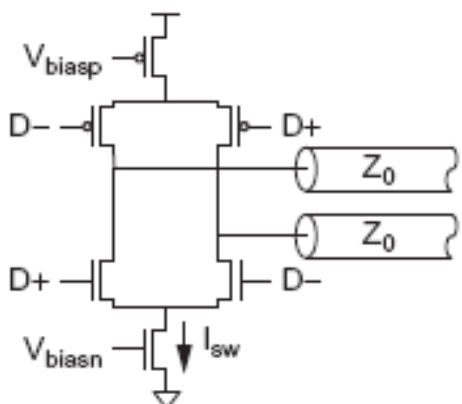
High-Speed I/O

- ❑ Transmit data faster than the flight time along the line
- ❑ Transmitters must generate very short pulses
- ❑ Receivers must be accurately synchronized to detect the pulses

High Speed Transmitters

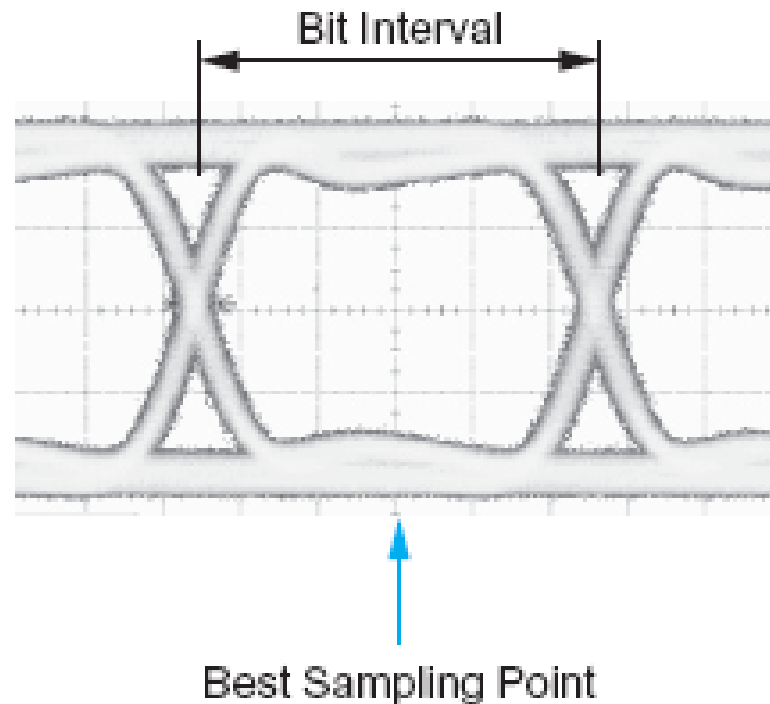
- ❑ How to handle termination?
 - High impedance current-mode driver + load term?
 - Or low-impedance driver + source termination
- ❑ Single-ended vs. differential
 - Single-ended uses half the wires
 - Differential is Immune to common mode noise
- ❑ Pull-only vs. Push-Pull
 - Pull-only has half the transistors
 - Push-pull uses less power for the same swing

High-Speed Transmitters

	Pull-Only	Push-Pull
Single-Ended	<p>Gunning Transceiver Logic (GTL)</p>  <p>The diagram shows a pull-up resistor $R = Z_0$ connected to a voltage source V_T. A switch current I_{sw} flows through the channel, which has an impedance Z_0. The voltage across the resistor is $V_{sw} = I_{sw} \times R$.</p>	 <p>The diagram shows a PMOS and NMOS transistor pair in a push-pull configuration. The PMOS gate is driven by V_{sw}. The NMOS gate is driven by a complementary signal. The output is connected to a channel with impedance Z_0.</p>
Differential	 <p>The diagram shows a differential pair of transistors. The gates are driven by $D+$ and $D-$. The tail current source is I_{sw} and the bias voltage is V_{bias}. The output is connected to a channel with impedance Z_0.</p> <p>Current Mode Logic (CML)</p>	 <p>The diagram shows a differential pair of transistors. The gates are driven by $D+$ and $D-$. The tail current source is I_{sw} and the bias voltage is V_{biasn}. The output is connected to a channel with impedance Z_0.</p> <p>Low-Voltage Differential Signalling (LVDS)</p>

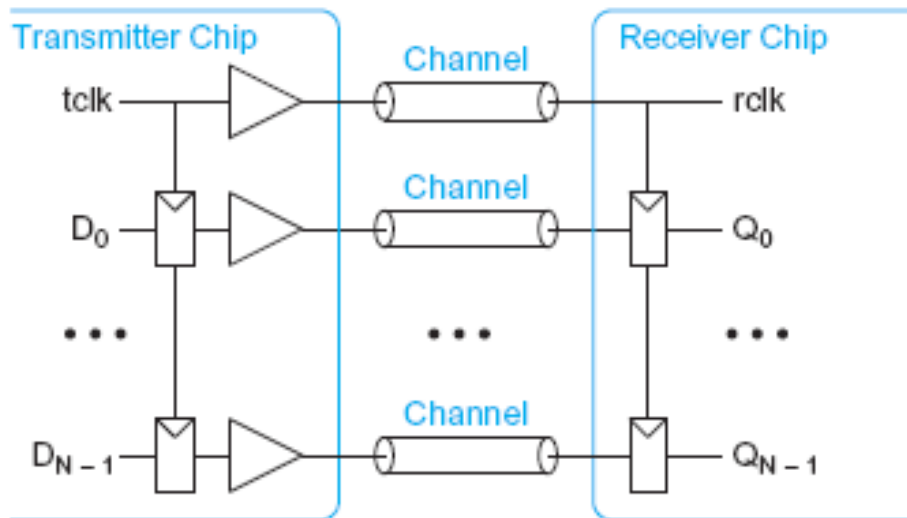
High-Speed Receivers

- ❑ Sample data in the middle of the bit interval
- ❑ How do we know when?



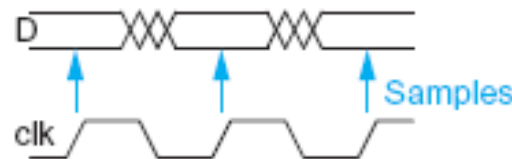
Source-Synchronous Clocking

- ❑ Send clock with the data
- ❑ Flight times roughly match each other
 - Transmit on falling edge of tclk
 - Receive on rising edge of rclk

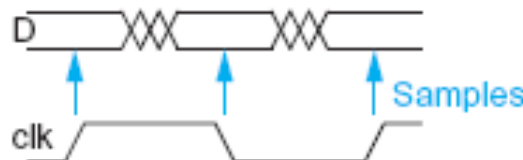


Single vs. Double Data Rate

- ❑ In ordinary single data rate (SDR) system, clock switches twice as often as the data

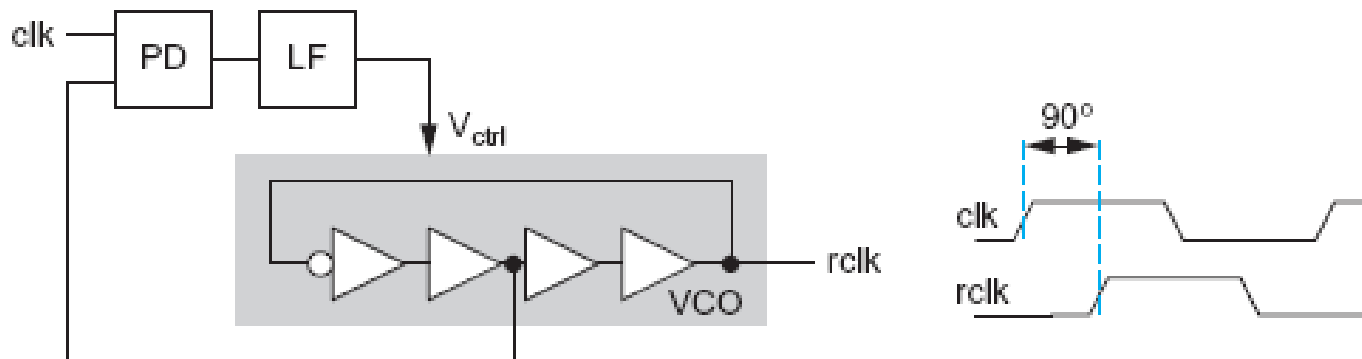


- ❑ If the system can handle this speed clock, the data is running at half the available bandwidth
- ❑ In double-data-rate (DDR) transmit and receive on both edges of the clock



Phase Alignment

- ❑ If the DDR clock is aligned to the transmitted clock, it must be shifted by 90° before sampling
- ❑ Use PLL



Mesochronous Clocking

- ❑ As speeds increase, it is difficult to keep clock and data aligned
 - Mismatches in trace lengths
 - Mismatches in propagation speeds
 - Different in clock vs. data drivers
- ❑ Mesochronous: clock and data have same frequency but unknown phase
 - Use PLL/DLL to realign clock to each data channel

Phase Calibration Loop

- ❑ Special phase detector compares clock & data phase

